



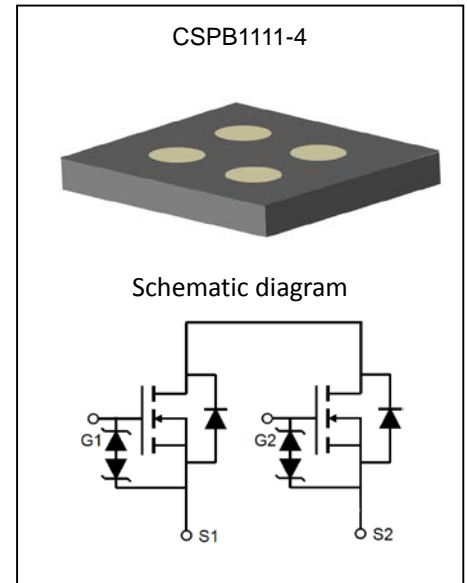
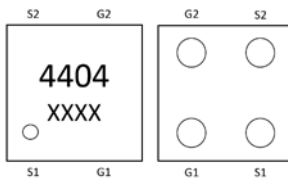
Product Summary

$V_{(BR)SSS}$	$R_{DS(on)TYP}$	I_{SS}
12V	22mΩ@4.5V	6A
	23mΩ@4.0V	
	24mΩ@3.8V	
	28mΩ@3.1V	
	34mΩ@2.5V	

Description

The GP4404SP uses advanced trench technology to provide excellent $R_{DS(on)}$, low gate charge and operation with gate voltages as low as 2.5V while retaining a 12V $V_{GS(MAX)}$ rating. It is ESD protected. This device is suitable for use as a unidirectional or bi-directional load switch, facilitated by its common-drain configuration.

Marking and pin assignment:



ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Source to Source Voltage	V_{SSS}	12	V
Gate-Source Voltage	V_{GSS}	± 8	V
Source Current(DC) ¹	I_S	6.0	A
Source Current (Pulse) ^{1,2}	I_{SP}	60	A
Total Dissipation	P_T	1.4	W
Channel Temperature	T_{ch}	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 to +150	$^{\circ}C$

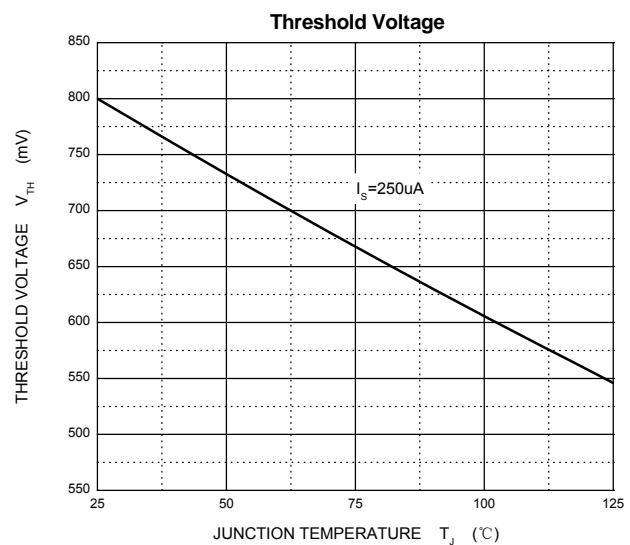
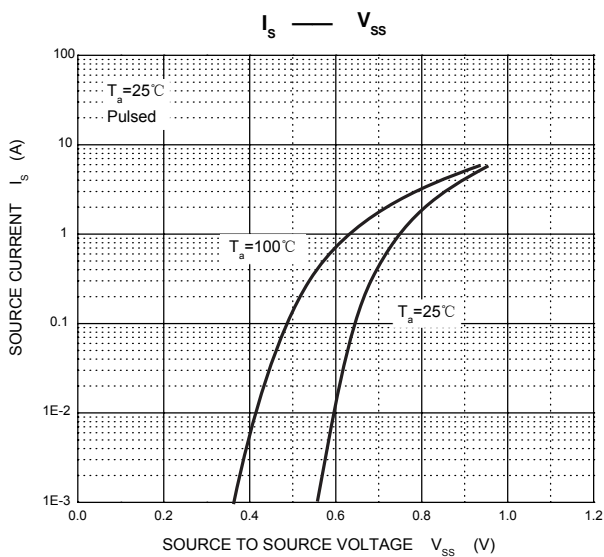
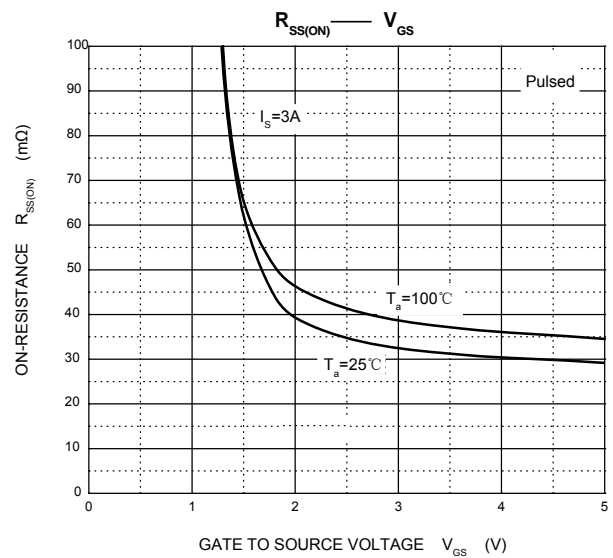
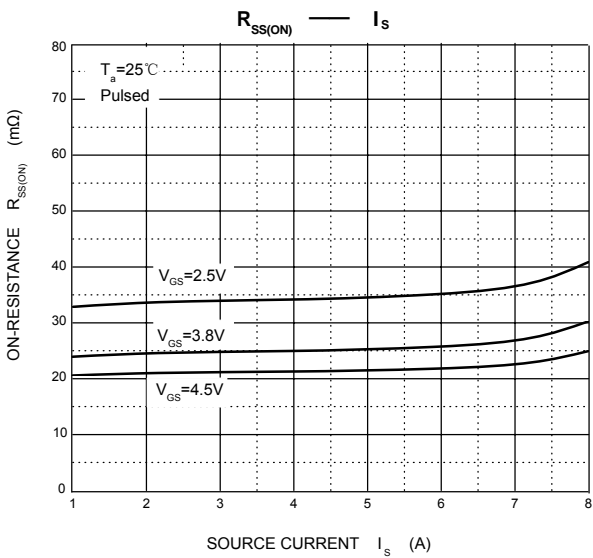
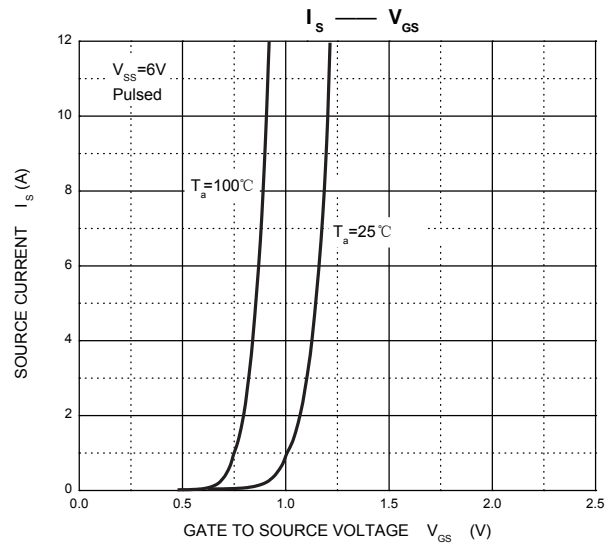
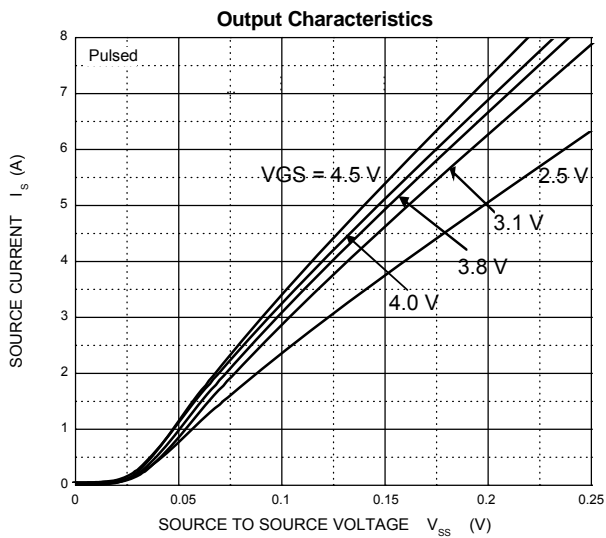
Note:

- 1、 Mounted on FR4 board (25.4mm × 25.4mm × t1.0mm) using the minimum recommended pad size (36μm Copper).
- 2、 $t = 10\mu s$, Duty Cycle $\leq 1\%$

MOSFET ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

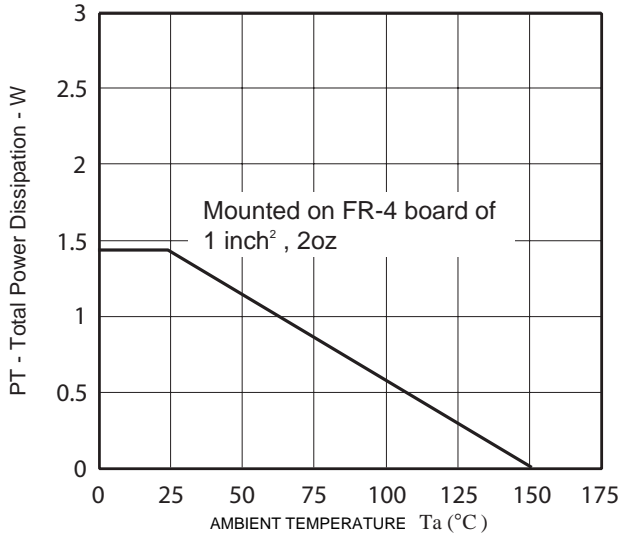
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Parameters						
Source to Source Breakdown Voltage	BV _{SSS}	I _S =250μA, V _{GS} =0V,	12			V
Zero- Gate Voltage Source Current	I _{SSS}	V _{SS} =20V, V _{GS} =0V			1	μA
Gate to Source Leakage Current	I _{GSS}	V _{SS} =0V, V _{GS} = ±8V			± 10	μA
Cutoff Voltage	V _{GS(off)}	V _{SS} =10V, I _S =250μA	0.5	0.8	1.3	V
Forward Transfer Admittance	y _{gF} s	V _{SS} =10V, I _S =3A	1	7		S
Static Source to Source On-Resistance	R _{SS(on)}	V _{GS} =4.5V, I _S =3A	14	22	28	mΩ
		V _{GS} =4.0V, I _S =3A	16	23	29	
		V _{GS} =3.8V, I _S =3A	18	24	30	
		V _{GS} =3.1V, I _S =3A	20	28	38	
		V _{GS} =2.5V, I _S =3A	22	34	48	
Turn-on Delay Time	t _{d(on)}	V _{SS} =10V, I _S =3A V _{GS} =4.5V		19		ns
Turn-on Rise Time	t _r			228		
Turn-Off Delay Time	t _{d(off)}			128		
Turn-Off Fall Time	t _f			109		
Total Gate Charge	Q _g	V _{SS} =10V, I _S =6A, V _{GS} =4.5V		7.2		nC
Diode Forward Voltage	V _{F(S-S)}	V _{GS} =0V, I _S =1A			1.2	V

Typical Electrical and Thermal Characteristics

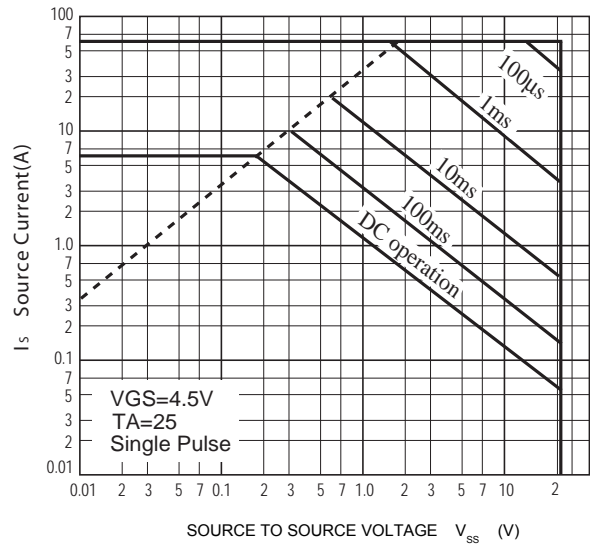


Typical Electrical and Thermal Characteristics

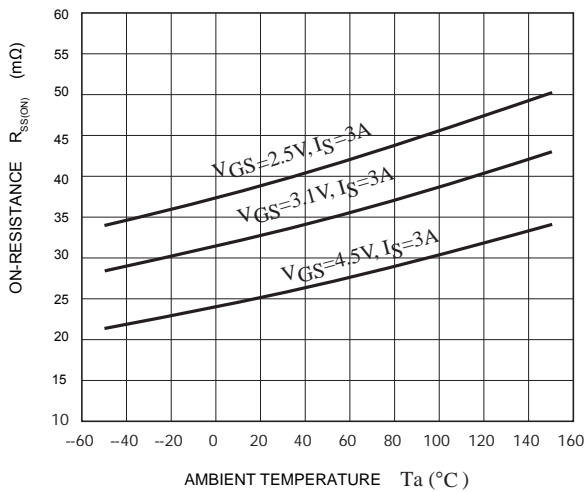
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



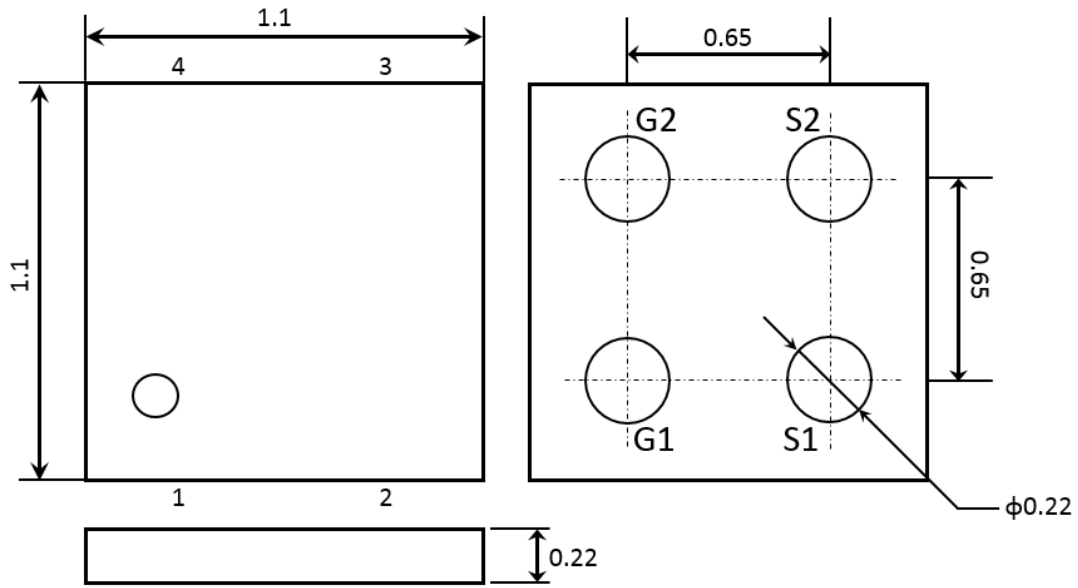
Maximum Safe Operating Area



$R_{SS(ON)}$ — T_a



CSPB1111-4 Package Outline Dimensions(Unit:mm)



单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)